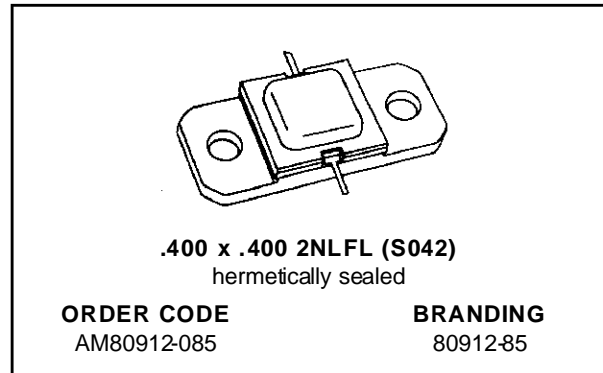


RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

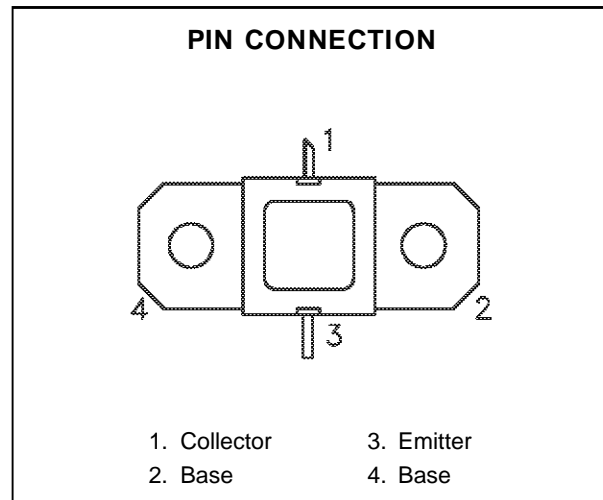
- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- 5:1 VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 85 W MIN. WITH 7.5 dB GAIN



DESCRIPTION

The AM80912-085 is designed for specialized avionics applications including JTIDS, where power is provided under pulse formats utilizing short pulse widths and high burst or overall duty cycles.

The AM80912-085 is housed in a unique BIG-PAC™ Hermetic Metal/Ceramic package with in-



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation* (T _C ≤ 100°C)	300	W
I _C	Device Current*	8.0	A
V _{CC}	Collector-Supply Voltage*	40	V
T _J	Junction Temperature (Pulsed RF Operation)	250	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance*	0.75	°C/W
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*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS ($T_{case} = 25^{\circ}C$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_C = 25mA$	$I_E = 0mA$	55	—	—	V
BV_{EBO}	$I_E = 10mA$	$I_C = 0mA$	3.5	—	—	V
BV_{CER}	$I_C = 25mA$	$R_{BE} = 10\Omega$	55	—	—	V
I_{CES}	$V_{BE} = 0V$	$V_{CE} = 35V$	—	—	20	mA
h_{FE}	$V_{CE} = 5V$	$I_C = 2A$	20	—	200	—

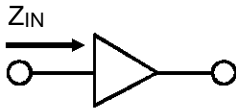
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 960 - 1215MHz$	$P_{IN} = 15W$	$V_{CC} = 35V$	85	—	—	W
η_c	$f = 960 - 1215MHz$	$P_{IN} = 15W$	$V_{CC} = 35V$	40	—	—	%
G_P	$f = 960 - 1215MHz$	$P_{IN} = 15W$	$V_{CC} = 35V$	7.5	—	—	dB

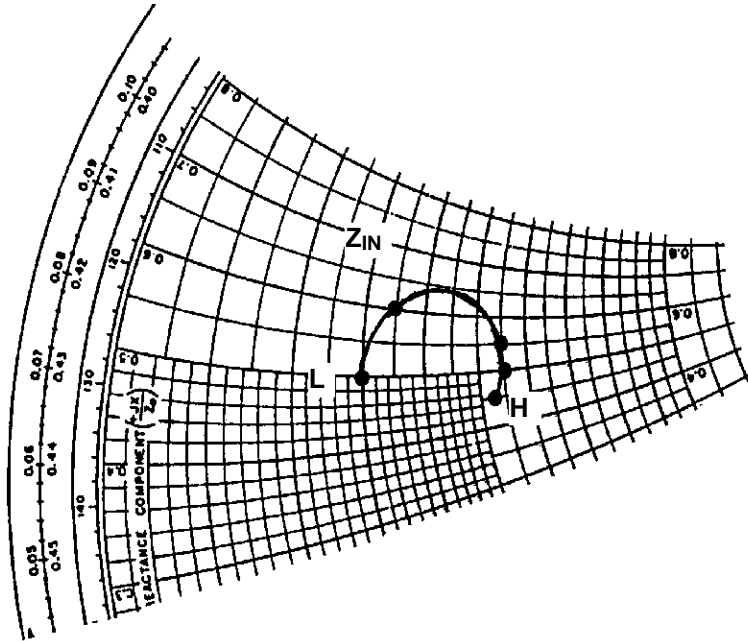
Note: Pulse format: 6.4 μS on 6.6 μS off, repeat for 3.3 ms, then off for 4.5125 ms
Duty Cycle: Burst 49.2%, overall 20.8%

IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

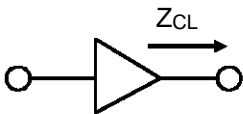


$P_{IN} = 15\text{ W}$
 $V_{CC} = 35\text{ V}$
 Normalized to 10 ohms

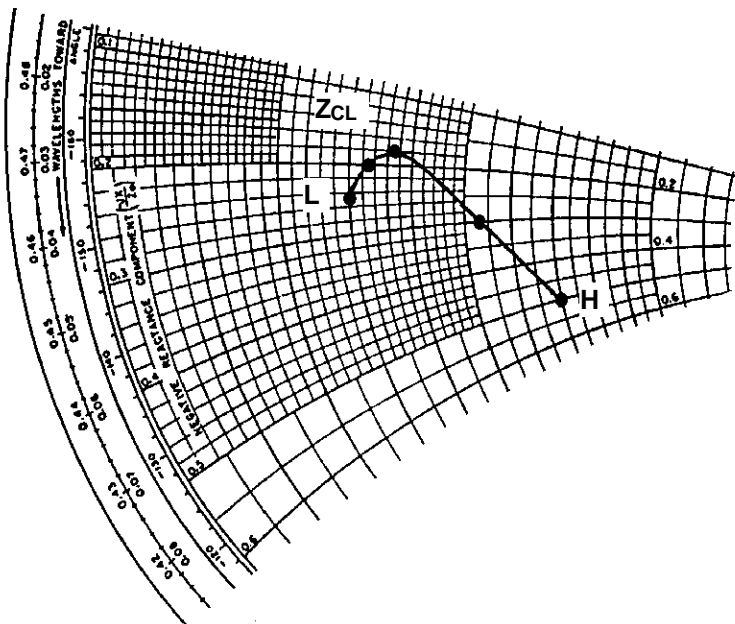


FREQ.	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$
L = 960 MHz	$3.0 + j 5.0$	$7.0 - j 5.0$
• = 1025 MHz	$3.5 + j 6.0$	$5.3 - j 3.0$
M = 1090 MHz	$5.5 + j 5.5$	$3.7 - j 1.8$
• = 1150 MHz	$5.5 + j 5.0$	$3.3 - j 2.0$
H = 1215 MHz	$5.3 + j 4.5$	$3.0 - j 2.5$

TYPICAL COLLECTOR LOAD IMPEDANCE

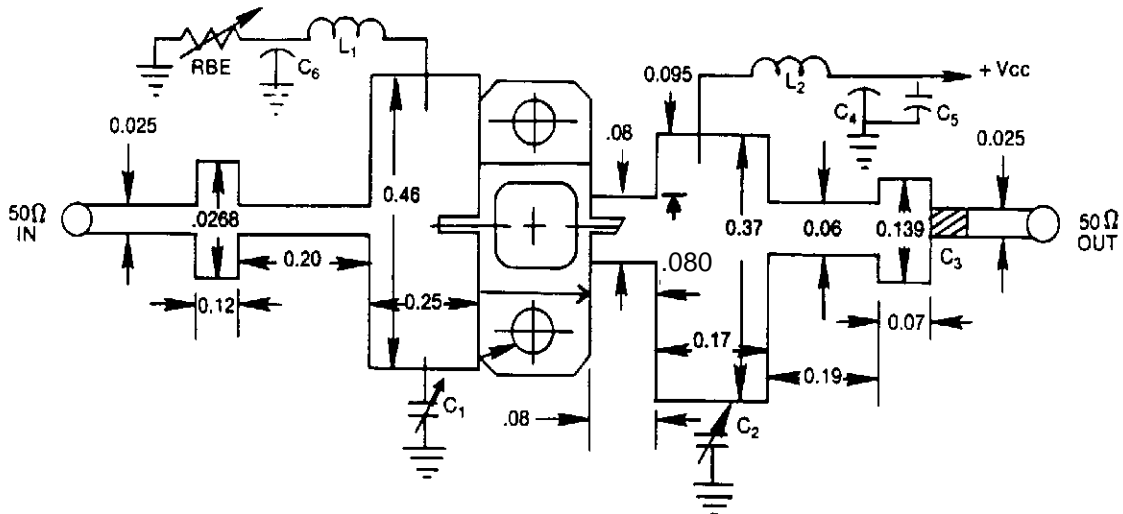


$P_{IN} = 15\text{ W}$
 $V_{CC} = 35\text{ V}$
 Normalized to 10 ohms



TEST CIRCUIT

Ref. Dwg. No. J-313119

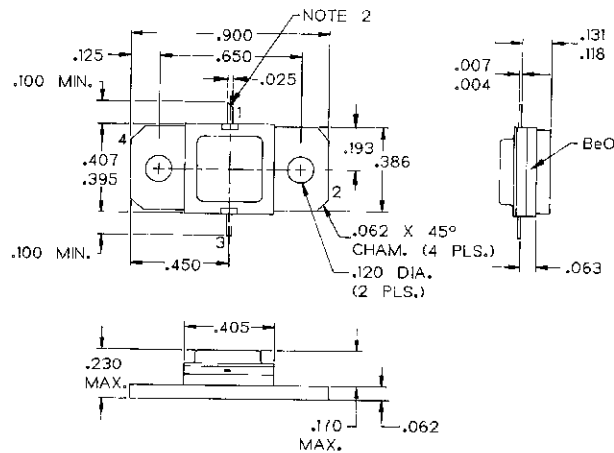


All dimensions are in inches.
Substrate material: .025 thick Al₂O₃ (Er = 9.6)

- | | |
|---|---|
| C1 : 0.3—3.5 pF Variable Johanson Capacitor or Equiv. | C5 : 100 MF, Electrolytic Capacitor, 50V |
| C2 : 0.3—3.5 pF Variable Johanson Capacitor or Equiv. | C6 : 1500 pF Erie RF Feedthrough, or Equiv. |
| C3 : 100 pF Chip Capacitor | L1 : No. 32 Wire, 4 Turns 1/16" I.D. |
| C4 : 1500 pF Erie RF Feedthrough, or Equiv. | L2 : No. 32 Wire, 4 Turns 1/16" I.D. |

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J113214F



- NOTES:
1. ALL TOLERANCE ± .010 EXCEPT WHERE NOTED; DIMENSIONS IN INCHES.
 2. COLLECTOR LEAD SLANT CUT.

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